Revision. 1

MOS FET

FC6B22160L1

Panasonic

FC6B22160L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

■ Features

- Low source-source ON resistance:Rss(on) typ. = 4.9 mΩ(VGS = 3.8 V)
- CSP(Chip Size Package)
- · RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 36

■ Packaging

Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

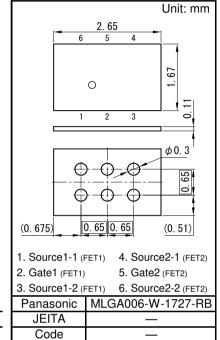
Parameter		Symbol	Rating	Unit	
Source-source Voltage		VSS	20	V	
Gate-source Voltage		VGS	±8	V	
Source Current	DC ^{*1}	IS1	8	Α	
	DC *2	IS2	17	Α	
	Pulse *3	ISp	80	Α	
Total Power Dissipation	DC *1	PD1	0.45	W	
Total Fower Dissipation	DC *2	PD2	2.1	W	
Channel Temperature		Tch	150	°C	
Storage Temperature Range		Tstg	-55 to +150	°C	
Thermal Resistance (ch-a)	DC ^{*1}	Rth1	278	°C/W	
	DC *2	Rth2	59	°C/W	

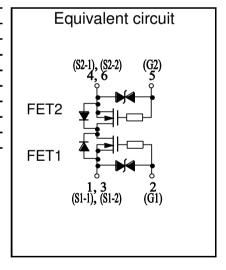
- Note *1 Mounted on FR4 board ($25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$) using the minimum recommended pad size ($36\mu\text{m}$ Copper).
 - *2 Mounted on Ceramic substrate (70 mm × 70 mm × t1.0 mm).
 - *3 $t = 10 \mu s$, Duty Cycle $\leq 1 \%$

Established: 2015-10-23

Revised

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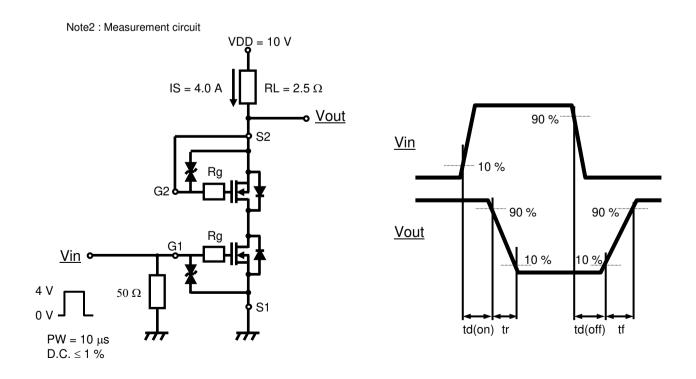
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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V	
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			±10	μА	
		$VGS = \pm 5 V$, $VSS = 0 V$			±1.0	μΑ	
Gate-source Threshold Voltage	Vth	IS = 1.1 mA, VSS = 10 V	0.35	0.90	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 4.0 A, VGS = 4.5 V	3.5	4.7	6.2	mΩ	
	RSS(on)2	IS = 4.0 A, VGS = 4.0 V	3.6	4.8	6.4		
	RSS(on)3	IS = 4.0 A, VGS = 3.8 V	3.7	4.9	6.6		
	RSS(on)4	IS = 4.0 A, VGS = 3.1 V	3.9	5.2	8.6		
	RSS(on)5	IS = 4.0 A, VGS = 2.5 V	4	6	11.8		
Body Diode Forward Voltage	VF(s-s)	IF = 4.0 A, VGS = 0 V		0.8	1.2	V	
Input Capacitance *1	Ciss			3250			
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 MHz		290		pF	
Reverse Transfer Capacitance *1	Crss			250			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		1.2			
Rise Time *1,*2	tr	IS = 4.0 A		2.4		μS	
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		8.1		μS	
Fall Time *1,*2	tf	IS = 4.0 A		3.9			
Total Gate Charge *1	Qg	VDD = 10 V		35			
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V,		5		nC	
Gate-drain Charge *1	Qgd	IS = 4.0 A		10			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- *1 Guaranteed by design, not subject to production testing
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



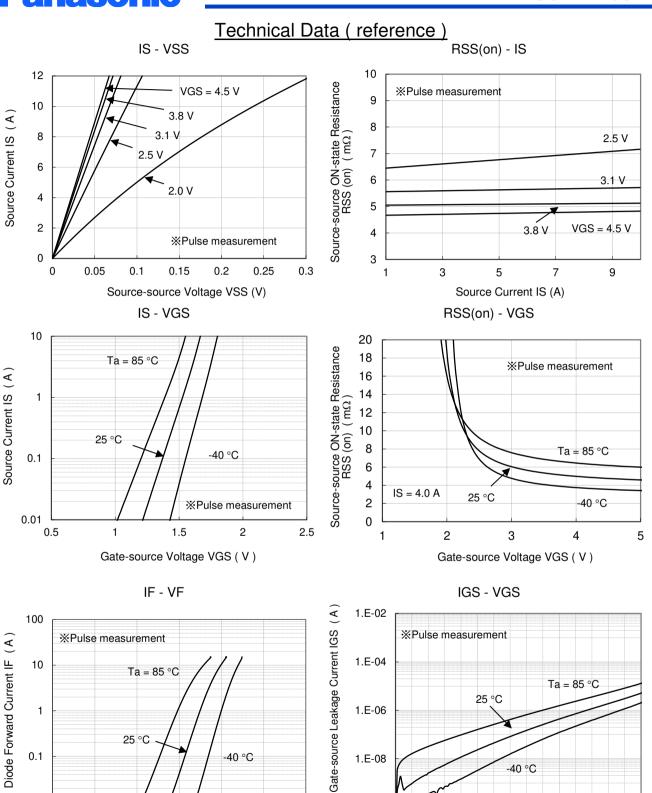
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1.E-10

5

Gate-source Voltage VGS (V)

1.2

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15

10

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0.01

0

0.4

0.2

0.6

Body Diode Forward Voltage VF (V)

8.0

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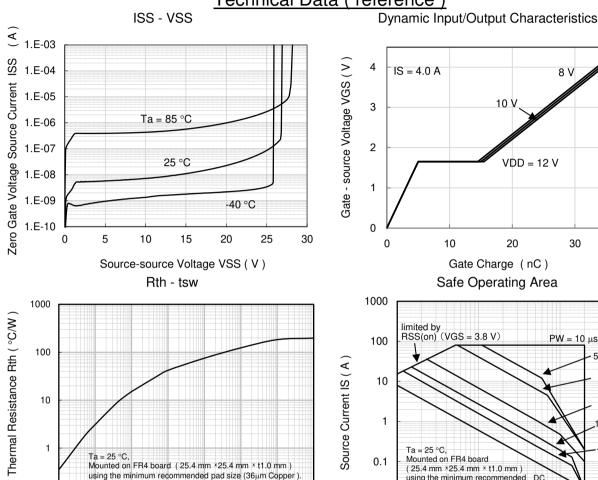
8 V

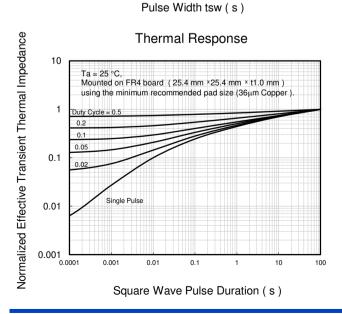
30

40

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 $PW = 10 \mu s$ -500 μs 1 ms 10 ms .100 ms Ta = 25 °C, Mounted on FR4 board (25.4 mm ×25.4 mm × t1.0 mm) using the minimum recomn pad size (36µm Copper). 0.01 100 0.1 Source-source Voltage VSS (V)

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0.1

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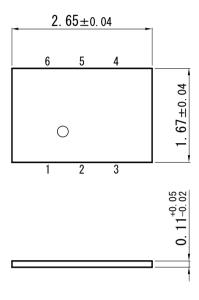
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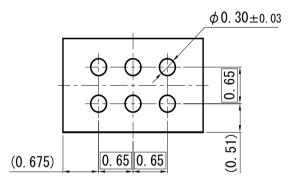
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■ Outline (MLGA006-W-1727-RB)

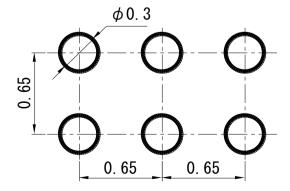
Unit: mm





■ Land Pattern (Reference)

Unit: mm



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